

TOSHIBA Transistor Silicon NPN Epitaxial Type (PCT process)

# 2SC3072

Strobe Flash Applications  
Medium Power Amplifier Applications

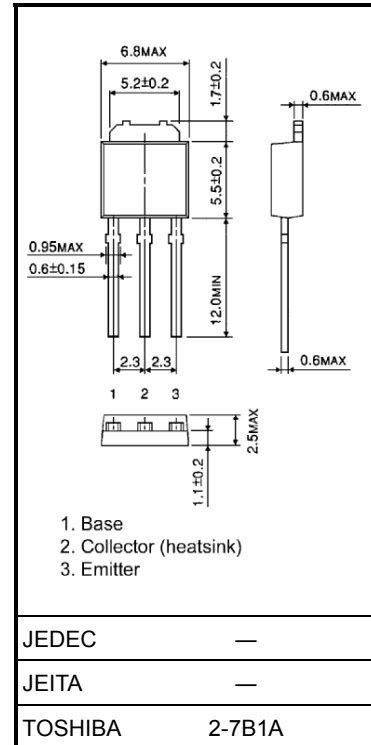
- High DC current gain  
:  $h_{FE} = 140$  to  $450$  ( $V_{CE} = 2$  V,  $I_C = 0.5$  A)  
:  $h_{FE} = 70$  (min) ( $V_{CE} = 2$  V,  $I_C = 4$  A)
- Low collector saturation voltage  
:  $V_{CE(sat)} = 1.0$  V (max) ( $I_C = 4$  A,  $I_B = 0.1$  A)
- High power dissipation  
:  $P_C = 10$  W ( $T_c = 25^\circ\text{C}$ ),  $P_C = 1.0$  W ( $T_a = 25^\circ\text{C}$ )

### Maximum Ratings ( $T_a = 25^\circ\text{C}$ )

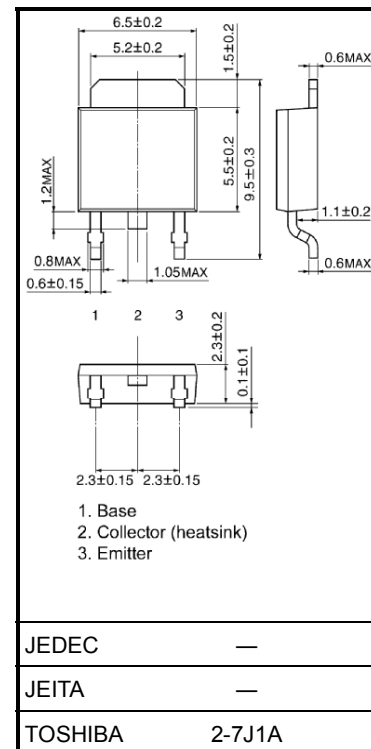
Characteristics		Symbol	Rating	Unit
Collector-base voltage		$V_{CBO}$	50	V
Collector-emitter voltage		$V_{CES}$	40	V
		$V_{CEO}$	20	
Emitter-base voltage		$V_{EBO}$	8	V
Collector current	DC	$I_C$	5	A
	Pulse (Note 1)	$I_{CP}$	8	
Base current		$I_B$	0.5	A
Collector power dissipation	$T_a = 25^\circ\text{C}$	$P_C$	1.0	W
	$T_c = 25^\circ\text{C}$		10	
Junction temperature		$T_j$	150	$^\circ\text{C}$
Storage temperature range		$T_{stg}$	-55 to 150	$^\circ\text{C}$

Note 1: Pulse test: Pulse width = 10 ms (max), duty cycle = 30% (max)

Unit: mm



Weight: 0.36 g (typ.)



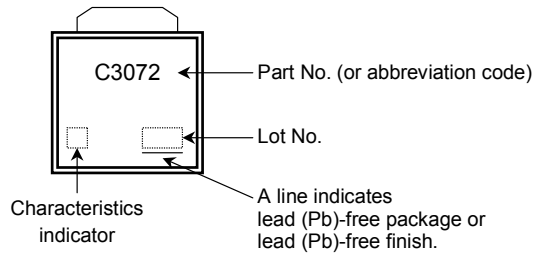
Weight: 0.36 g (typ.)

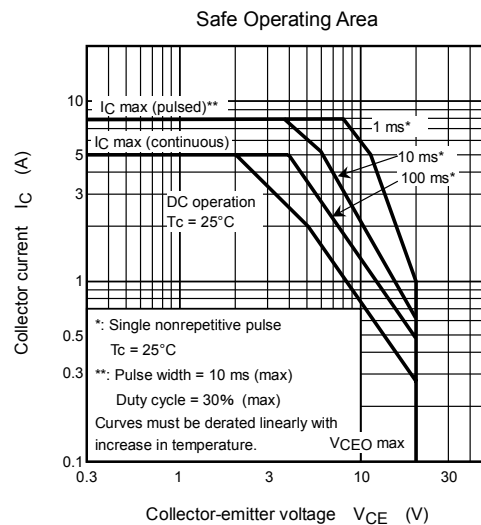
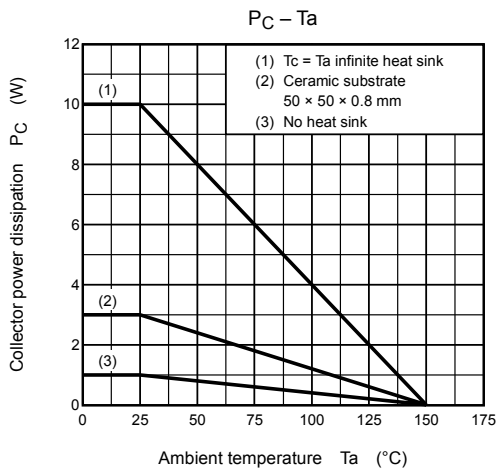
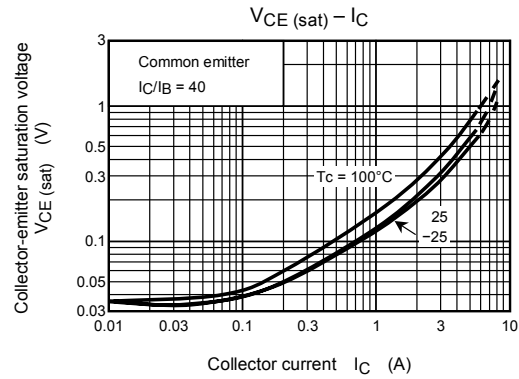
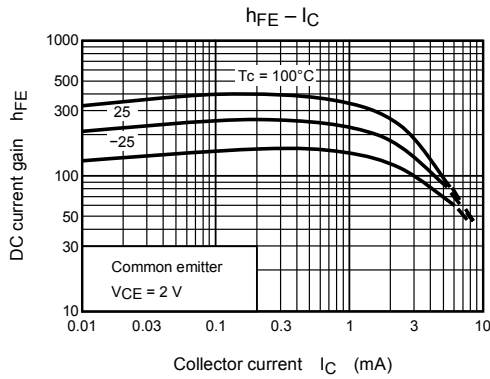
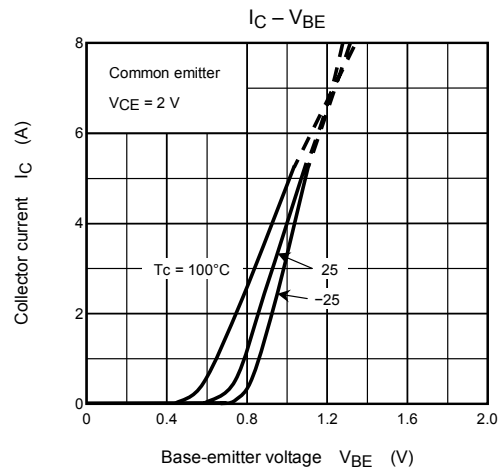
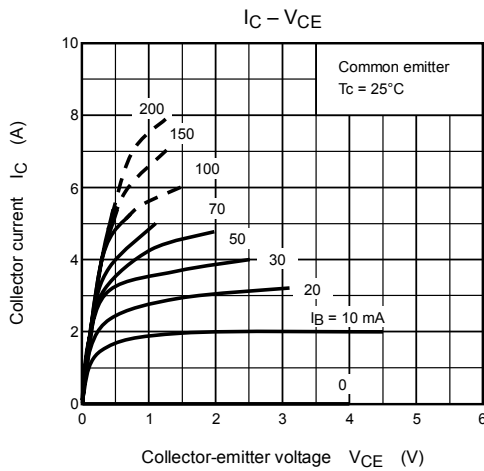
**Electrical Characteristics (Ta = 25°C)**

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	$I_{CBO}$	$V_{CB} = 40\text{ V}, I_E = 0$	—	—	100	nA
Emitter cut-off current	$I_{EBO}$	$V_{EB} = 8\text{ V}, I_C = 0$	—	—	100	nA
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 10\text{ mA}, I_B = 0$	20	—	—	V
DC current gain	$h_{FE(1)}$ (Note 2)	$V_{CE} = 2\text{ V}, I_C = 0.5\text{ A}$	140	—	450	
	$h_{FE(2)}$	$V_{CE} = 2\text{ V}, I_C = 4\text{ A}$	70	—	—	
Collector emitter saturation voltage	$V_{CE(sat)}$	$I_C = 4\text{ A}, I_B = 0.1\text{ A}$	—	—	1.0	V
Base-emitter voltage	$V_{BE}$	$V_{CE} = 2\text{ V}, I_C = 4\text{ A}$	—	—	1.5	V
Transition frequency	$f_T$	$V_{CE} = 2\text{ V}, I_C = 0.5\text{ A}$	—	100	—	MHz
Collector output capacitance	$C_{ob}$	$V_{CB} = 10\text{ V}, I_E = 0, f = 1\text{ MHz}$	—	40	—	pF

Note 2:  $h_{FE(1)}$  classification A: 140 to 240, B: 200 to 330, C: 300 to 450

**Marking**





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